Transistors

Panasonic

# 2SC4562G

### Silicon NPN epitaxial planar type

For high-frequency amplification Complementary to 2SA1748G

#### Features

- High transition frequency f<sub>T</sub>
- $\bullet$  Small collector output capacitance (Common base, input open circuited)  $C_{ob}$
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	v
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	V
Collector current	I <sub>C</sub>	50	mA
Collector power dissipation	P <sub>C</sub>	150	mW
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	¢°C

#### Package

- Code
- SMini3-F2
- Marking Symbol: AM
- Pin Name
  - 1: Base
  - 2: Emitter
  - 3: Collector

#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	50	2		V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 1 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	5			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 10 V, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 10 \text{ V}, I_B = 0$			100	μΑ
Forward current transfer ratio *	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	200		500	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1 \text{ mA}$		0.06	0.30	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		250		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

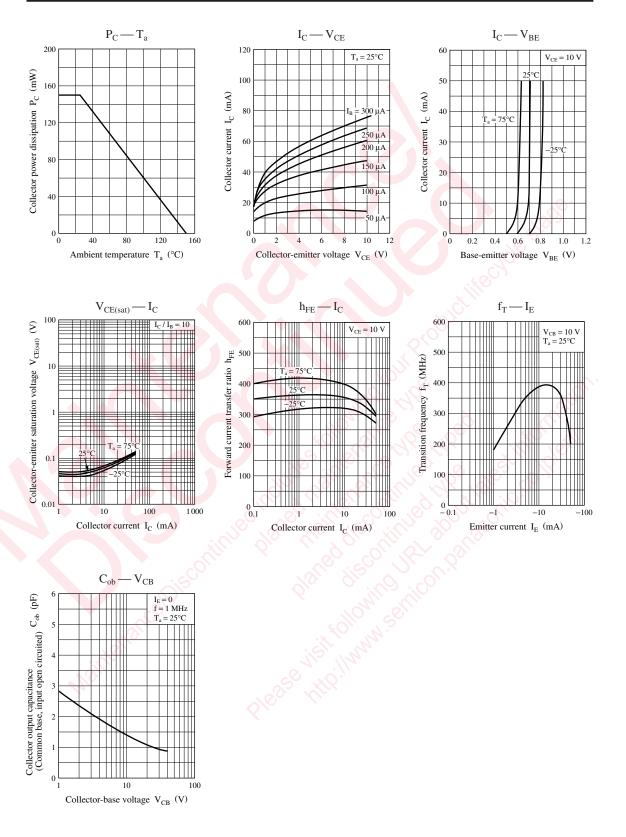
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. \*: Rank classification

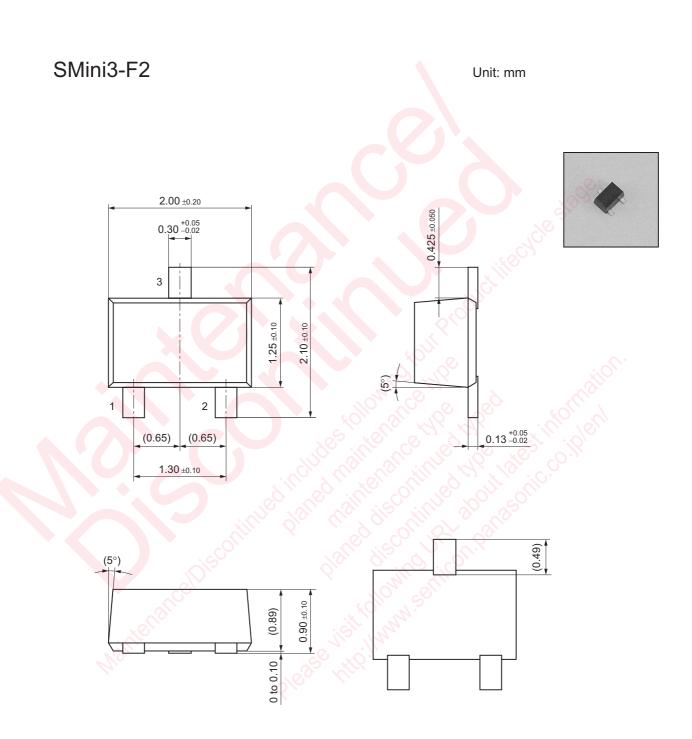
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	Rank	Q			

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	$\mathbf{h}_{\mathrm{FE}}$	200 to 400	250 to 500

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